

AMENDMENTS TO THE CLAIMS

Listing Of Claims

Claims 1-33 (Canceled)

34. (previously presented) A method for fabricating an interconnect for electrically engaging a semiconductor component with at least one bumped contact having a radius comprising:

providing a substrate having a surface;

forming a plurality of leads on the surface configured to electrically engage and support the bumped contact, the leads having terminal portions and support portions;

forming a recess in the surface configured to cantilever the terminal portions over the recess with the support portions on the surface supporting the terminal portions for movement within the recess during electrical engagement of the bumped contact; and

shaping the terminal portions with a curvature approximately equal to the radius of the bumped contact.

35. (previously presented) The method of claim 34 further comprising forming outer layers on the terminal portions configured to provide a non bonding surface for the bumped contact.

36. (withdrawn) The method of claim 34 wherein forming the plurality of leads comprises attaching a polymer tape to the substrate with the leads formed thereon.

37. (withdrawn) The method of claim 34 wherein forming the plurality of leads comprises etching beams in

the substrate within the recess and covering the beams with conductive layers.

38. (previously presented) The method of claim 34 wherein the substrate comprises a semiconductor material and the forming the recess step comprises etching.

39. (currently amended) A method for fabricating an interconnect for electrically engaging a semiconductor component having at least one bumped contact having a shape comprising:

providing a substrate having a surface;

forming a plurality of leads on the substrate configured to electrically engage and support the bumped contact, the leads having terminal portions and support portions, each terminal portion having at least one projection configured to penetrate the bumped contact;

~~with the projections thereon and support portions;~~

~~etching~~ forming a recess in the surface configured to cantilever the terminal portions over the recess with the support portions on the surface supporting the terminal portions for movement within the recess during electrical engagement of the bumped contact; and

shaping the terminal portions with a curvature matching the shape of the bumped contact.

40. (previously presented) The method of claim 39 wherein the shaping step comprises pressing the leads with a tool.

41. (previously presented) The method of claim 39 wherein the shaping step comprises heating the leads.

42. (withdrawn) The method of claim 39 further comprising shaping the leads with a radius of curvature corresponding to a diameter of the bumped contact.

43. (previously presented) The method of claim 39 further comprising forming a connecting segment on the substrate electrically connecting the leads, a conductive via in the substrate in electrical communication with the connecting segment and a contact on the substrate in electrical communication with the conductive via.

Claims 44-48 (canceled)

49. (currently amended) A method for fabricating an interconnect for electrically engaging a semiconductor component having a plurality of bumped contacts comprising:

providing a substrate;

forming a plurality of interconnect contacts on the substrate configured to electrically engage the bumped contacts, each interconnect contact comprising a plurality of leads having terminal portions and projections on the terminal portions configured to penetrate oxide layers on the bumped contacts;

forming outer layers on the terminal portions and projections configured to provide non-bonding surfaces for the bumped contacts;

forming a plurality of recesses in the substrate proximate to the leads configured to cantilever the terminal portions of the leads for movement within the recesses during the electrical engagement; and

shaping the terminal portions to match a shape of a bumped contact.

50. (previously presented) The method of claim 49 wherein the outer layers comprise a conductive polymer.

51. (previously presented) The method of claim 49 wherein the projections comprise blades.

52. (withdrawn) The method of claim 49 wherein the forming the conductive vias step comprises laser machining.

Claims 53-58 (canceled)